

Notice of References Cited

Applicant/Patent

Ahn et al.

Application/Control No.

09/755,071

Examiner

George C. Eckert II

Art Unit

2815

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	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²	
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NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
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^{*} A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.